

## Amendments to the Claims

1-8. (Cancelled)

9. (New) A method of forming a copper oxide thin film low-friction material containing CuO mainly in its composition and having friction coefficients of 0.06 or less both in the atmosphere and in vacuum at  $3\times10^{-5}$  Pa, which comprises forming the copper oxide thin film low-friction material on a substrate for deposition, by plasma sputtering in vacuum at  $1\times10^{-4}$  to  $1\times10^{-6}$  Pa, while using CuO as a target and introducing a mixed gas of a rare gas and oxygen containing oxygen at a partial pressure of 85% or less.

10. (New) The film-forming method according to Claim 9, wherein the crystal of the copper oxide thin film is oriented.

11. (New) A copper oxide thin film low-friction material formed on a substrate, containing mainly CuO in its composition and having friction coefficients of 0.06 or less both in the atmosphere and in vacuum at  $3\times10^{-5}$  Pa.

12. (New) The copper oxide thin film low-friction material according to Claim 11, formed by plasma deposition.

13. (New) The copper oxide thin film low-friction material according to Claim 11, wherein the crystal of the copper oxide thin film is oriented.

14. (New) The copper oxide thin film low-friction material according to Claim 12, wherein the crystal of the copper oxide thin film is oriented.

15. (New) A sliding device, having a sliding face coated with the copper oxide thin film low-friction material according to Claim 11.

16. (New) A sliding device, having a sliding face coated with the copper oxide thin film low-friction material according to Claim 12.

17. (New) A sliding device, having a sliding face coated with the copper oxide thin film low-friction material according to Claim 13.